



How to preserve the Kramers-Kronig relation in inelastic atomistic quantum transport calculations

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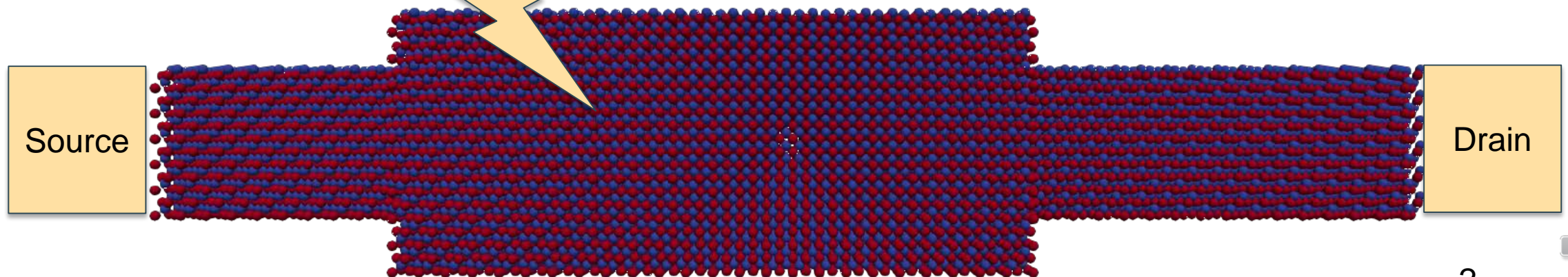
$$G^R = (E - H - \Sigma^R)^{-1}$$
$$G^< = G^R \Sigma^< G^{R\dagger}$$

Self-energies represent external perturbations in atomic devices

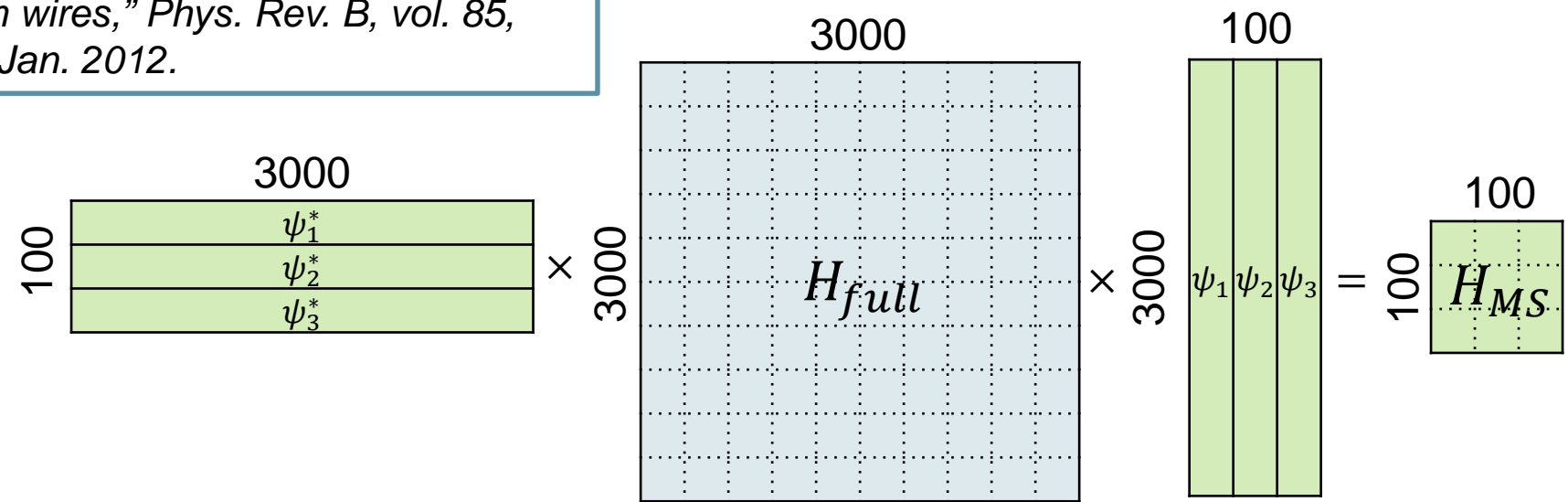
- Electrons entering/exiting device (lead/contact self-energy)
- **Incoherent scattering** phenomena, e.g., phonons

$$\Sigma^R = G^R D^R + G^R D^< + G^< D^R$$

Computationally expensive



Clever mode filtering method detailed in:
G. Mil'nikov, et al., "Equivalent transport models in atomistic quantum wires," Phys. Rev. B, vol. 85, no. 3, p. 035317, Jan. 2012.



3 nm × 3 nm cross section device using 10-orbital tight binding:
 ~3000 × 3000 matrices (single unit cell)
 $O(N^3) = 2.7 \times 10^{10}$ operations

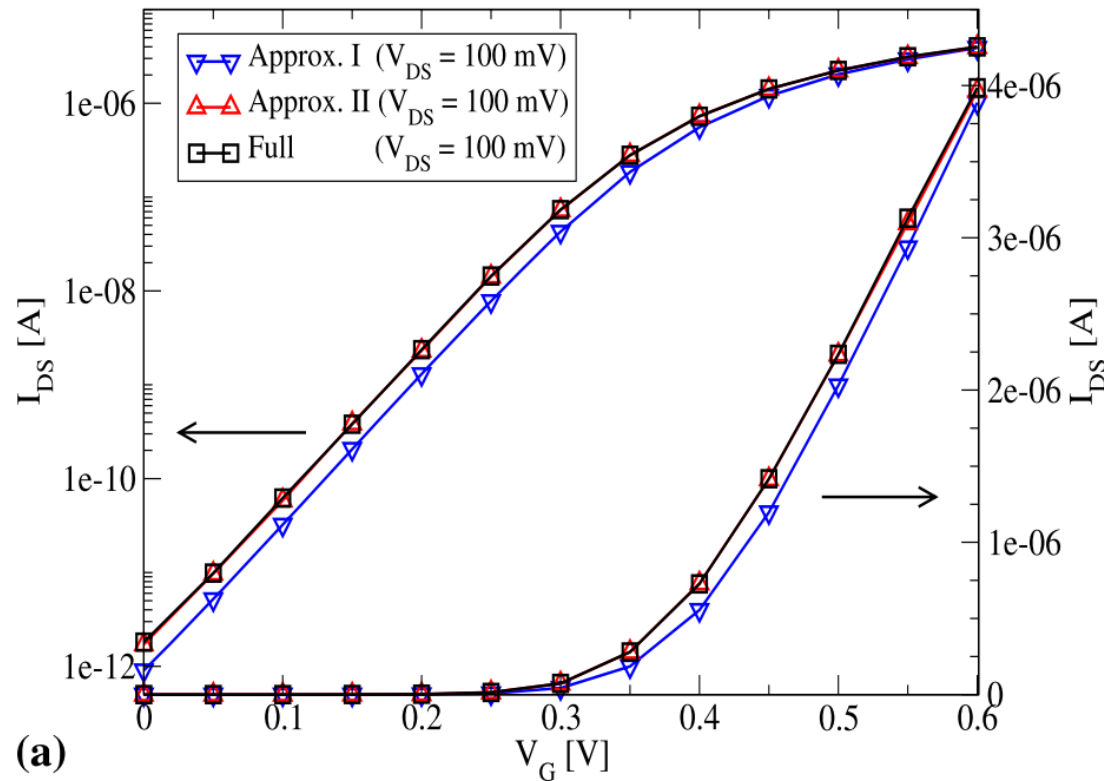
Rank reduced by ~97%
3% reduction ratio

3 nm × 3 nm device using 100 modes:
 100 × 100 matrices
 $O(N^3) = 10^6$ operations

Huge reduction in computational complexity



- Approx. I: No real part
- Approx. II: Approximation avoids principal value integral
- Full: Includes principal value integral



- Common in mode space to **avoid the real part of Σ^R**

Take advantage of mode space and solve Σ^R **exactly**

A. Esposito, M. Frey, and A. Schenk, "Quantum transport including nonparabolicity and phonon scattering: Application to silicon nanowires," *J. Comput. Electron.*, vol. 8, no. 3–4, pp. 336–348, 2009.



$$\text{Im}[\Sigma^R(E)] = \frac{1}{2}(\Sigma^>(E) - \Sigma^<(E))$$

- Responsible for dephasing of electrons

$$\text{Re}[\Sigma^R(E)] = \frac{i}{\pi} \mathcal{P} \int dE' \frac{\text{Im}[\Sigma^R(E')]}{E - E'}$$

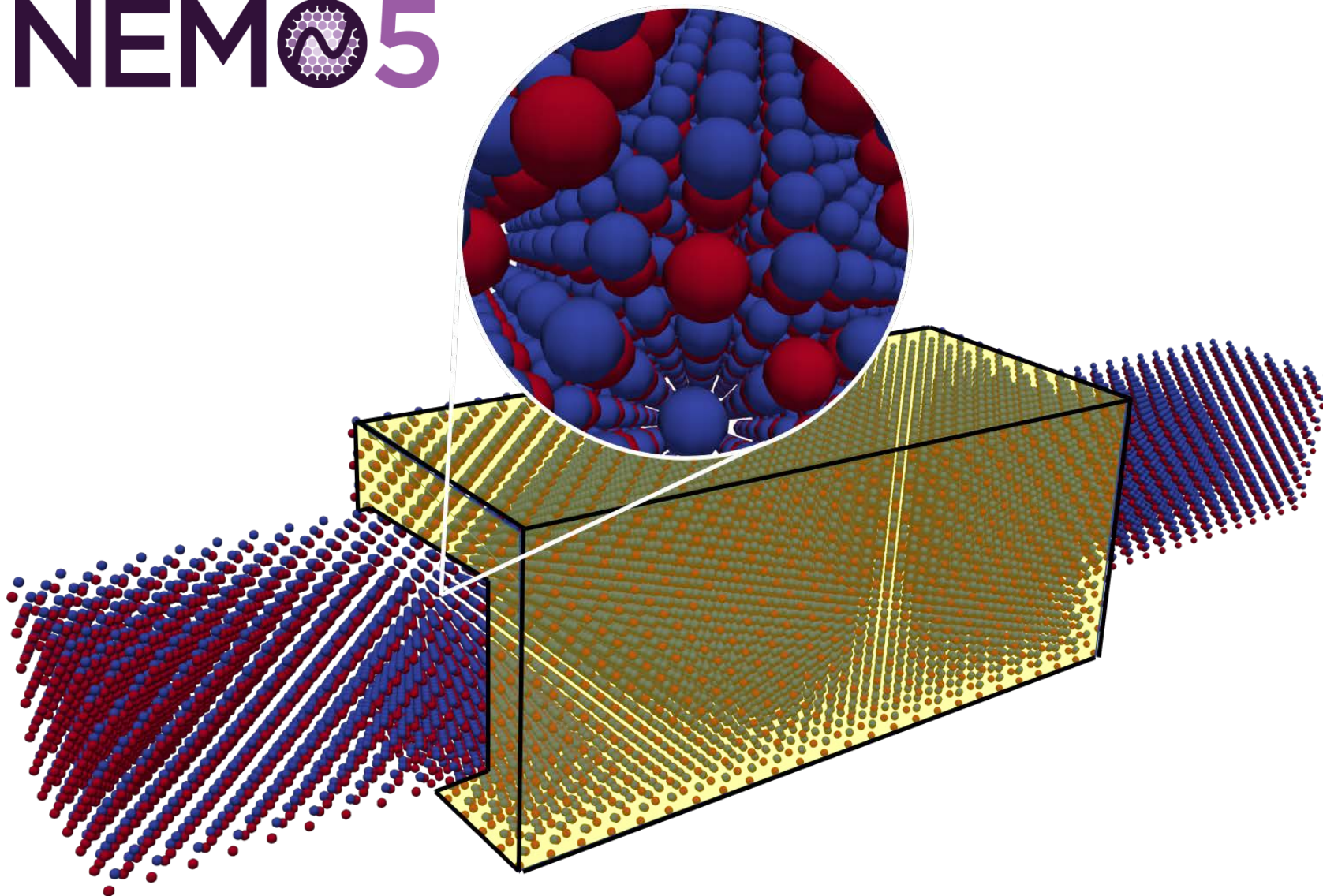
- Responsible for shifting resonance energies
- In the form of Kramers-Kronig relations/Hilbert transform

$$H(u)(t) = \frac{1}{\pi} \int_{-\infty}^{\infty} \frac{u(\tau)}{t - \tau} d\tau$$

Hilbert transform in mode space is faster: < 1% of operations

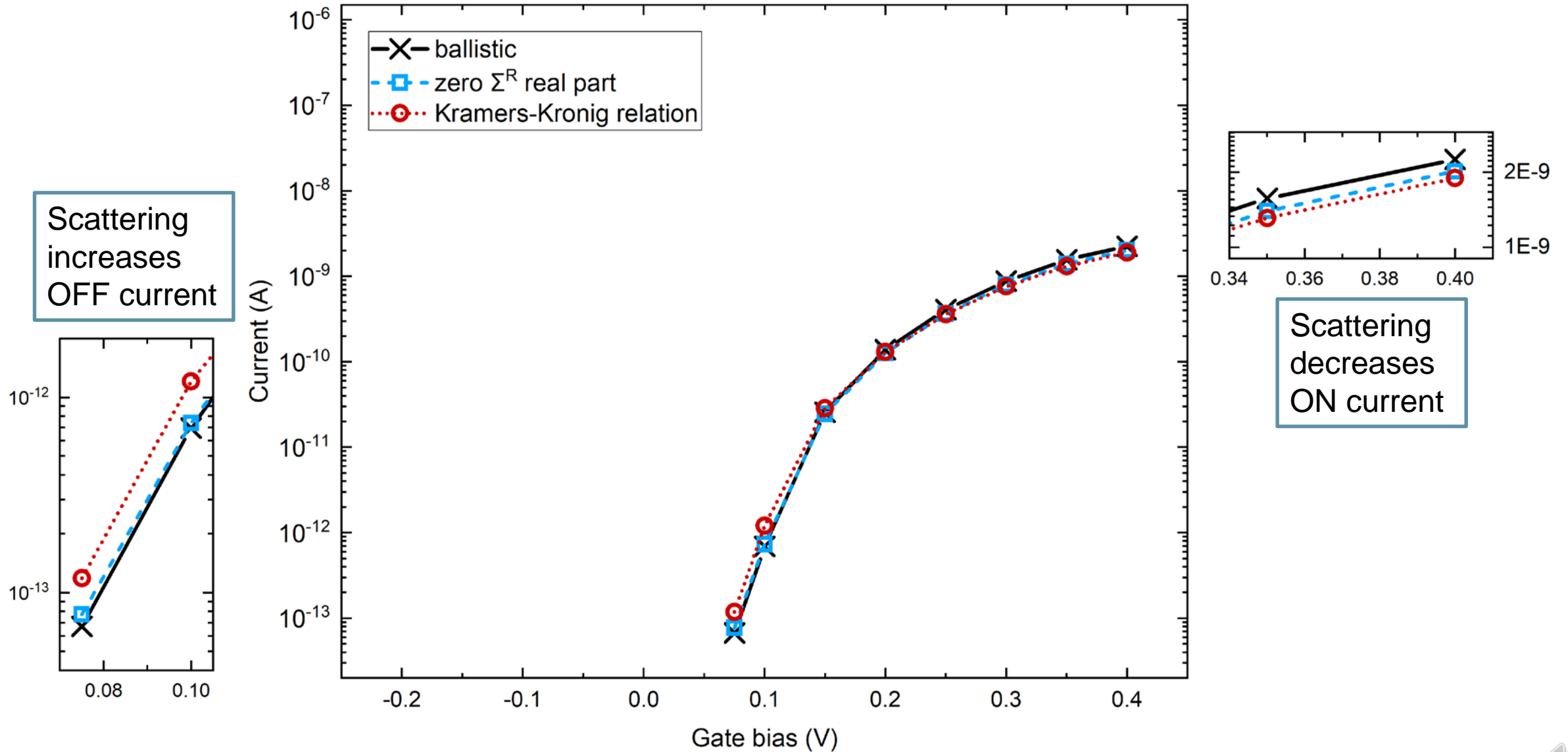


NEMO5



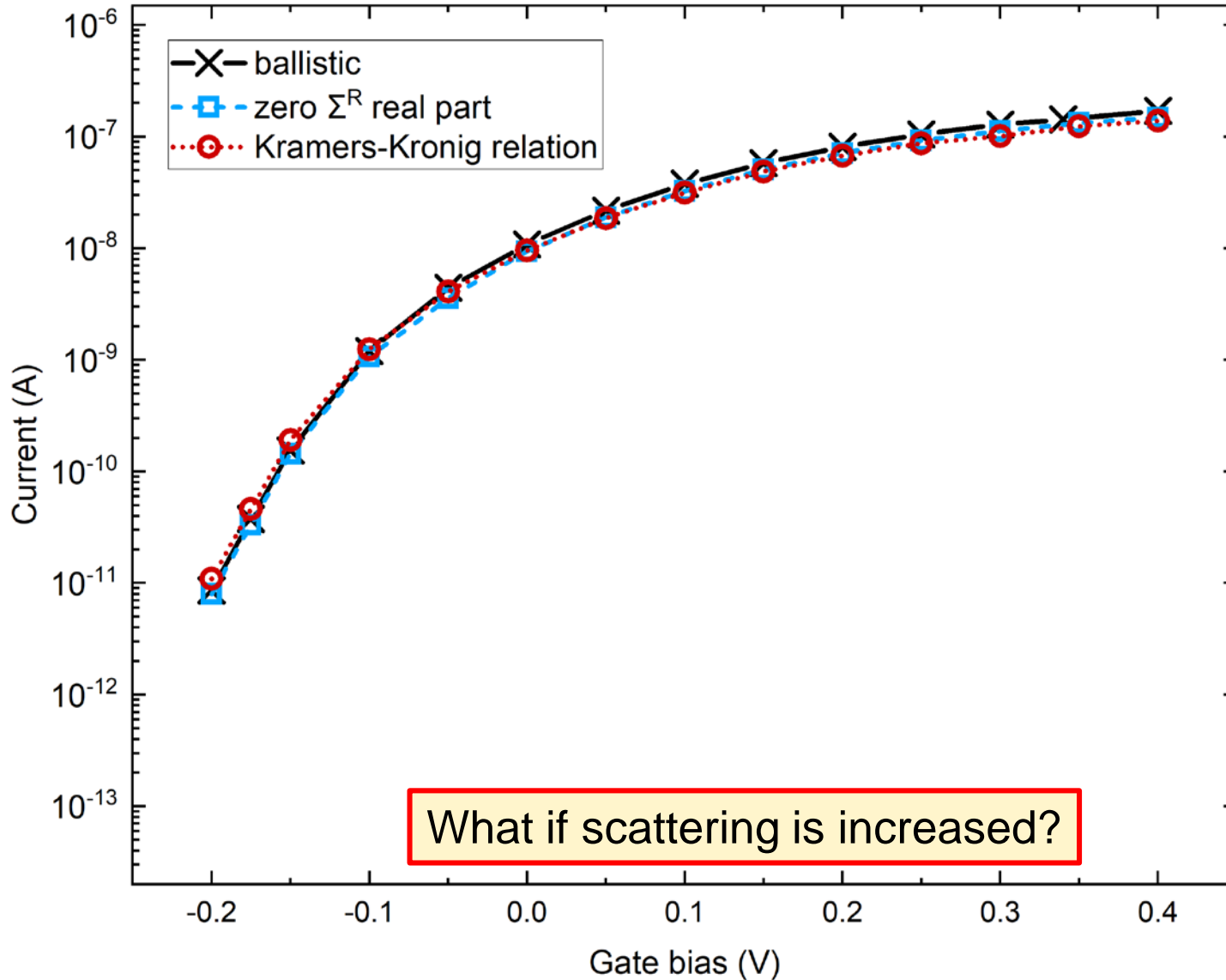
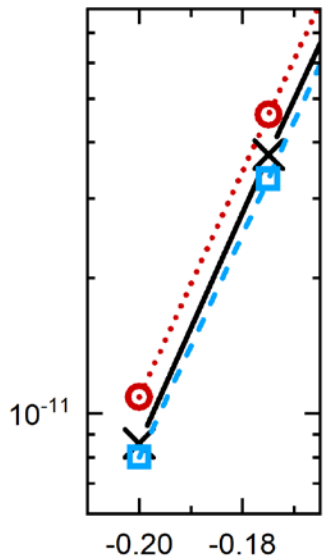
- InAs tunnel FET
- Atomistic tight binding
- Acoustic phonon scattering, optical phonon scattering, polar-optical phonon scattering
- Three cases:
 - Ballistic only
 - Scattering, zero real Σ^R
 - Scattering Σ^R from Kramers-Kronig relation
- All in mode space



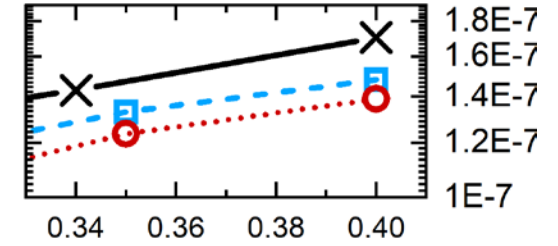


$Re\{\Sigma^R\} = 0$
decreases
OFF current

$Re\{\Sigma^R\} \neq 0$
increases
OFF current



What if scattering is increased?

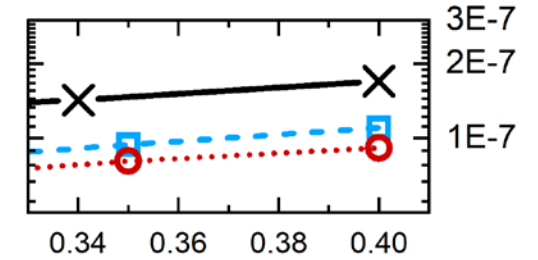
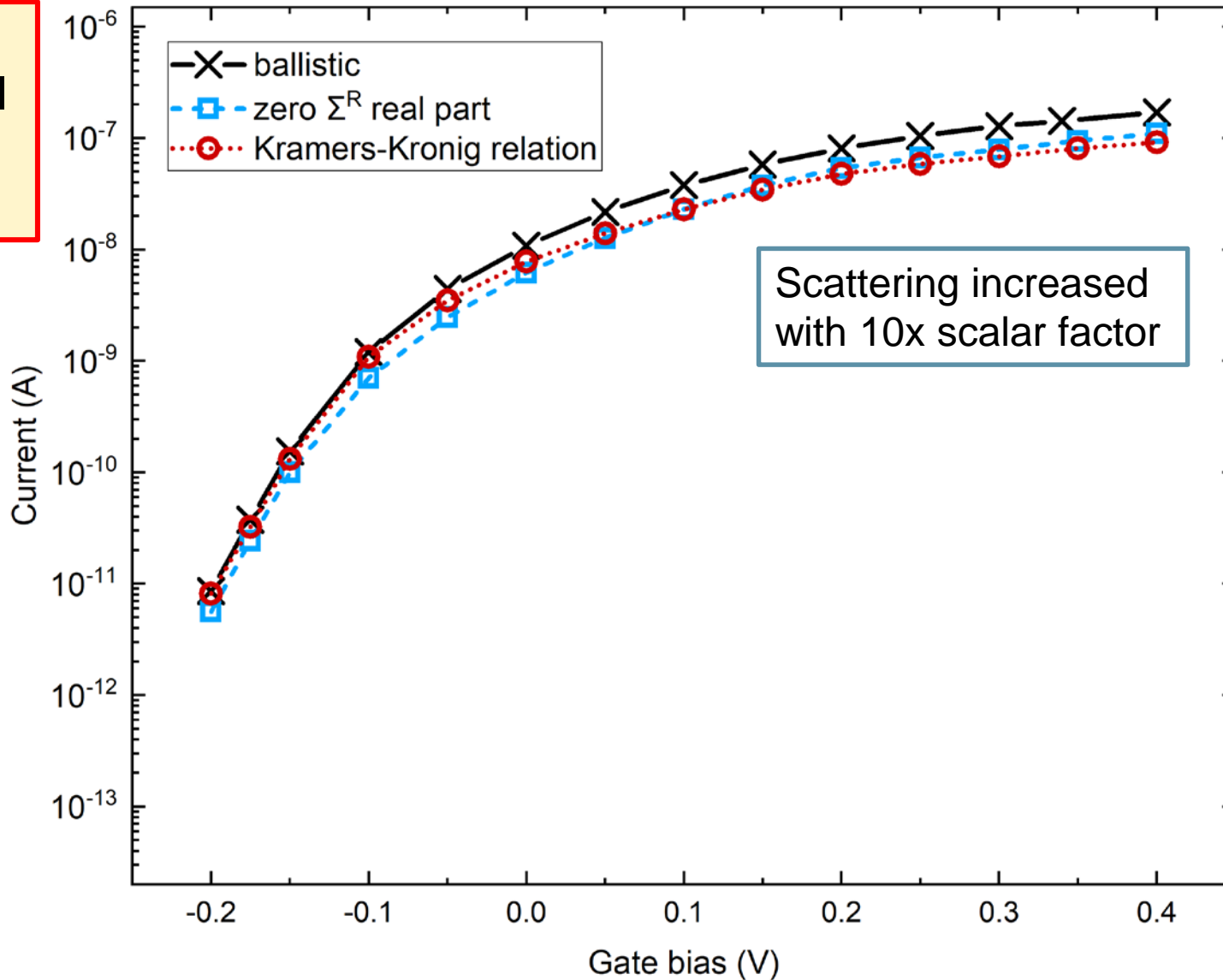
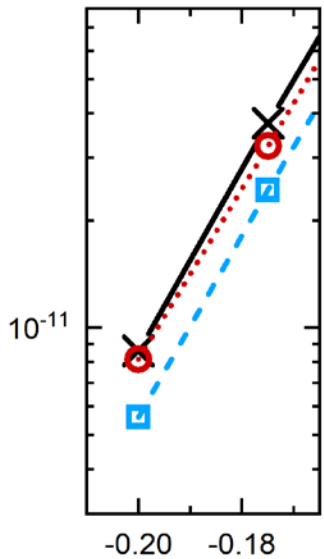


Scattering
decreases
ON current



Situation-dependent; real part of Σ^R must be included

Scattering decreases OFF current



Scattering decreases ON current

Greater effect from real part

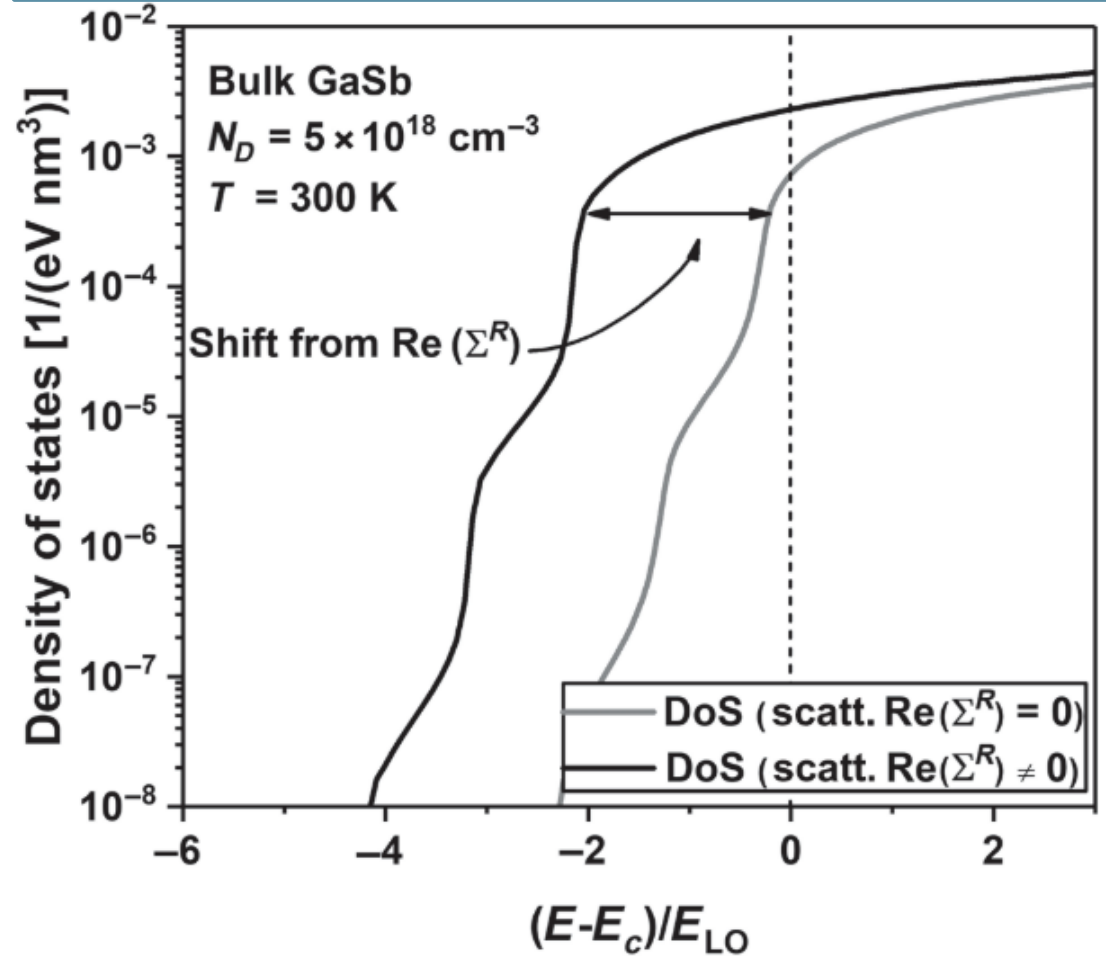


Previous NEMO5 results, shown in IWCN 2019

Previous results did not include mode space, but current results do

Exact solution of Σ^R , in mode space, available in NEMO5

Energy-resolved conduction band density of states



P. Sarangapani, et al., "Band-tail Formation and Band-gap Narrowing Driven by Polar Optical Phonons and Charged Impurities in Atomically Resolved III-V Semiconductors and Nanodevices," *Phys. Rev. Appl.*, vol. 12, no. 4, p. 1, 2019.

NEMO5

SILVACO

The screenshot shows the Silvaco website's navigation bar with the logo and menu items: Tools, IP, Solutions, Services, Support, Corporate, and a search icon. The main content area features a header for 'Victory Atomistic' with a background image of a nanostructure. Below the header is a navigation bar with icons for Overview, Resources, Videos, News/Blogs, and Customers. The main text describes the 'Victory Atomistic Device and Nanostructure Simulator' as a hybrid quantum and semi-classical solution for nanotechnology products. It lists benefits such as scalability from a few atoms to a million-atom structure, a self-consistent Schrödinger-Poisson solver, and a Non-Equilibrium Green's Functions (NEGF) solver. On the right side, there is a vertical list of simulation categories: TCAD, Process Simulation, Device Simulation, Atomistic Simulation, Meshing & Solid Modeling, and Parasitic Extraction.

<https://silvaco.com/tcad/atomistic-simulation/>

Thank you!

